

LISTING OF THE CLAIMS

1. (Original) A process of growing a thin film of Al_2O_3 on a substrate by a sequential vapor deposition process comprising a plurality of cycles, each cycle comprising:
 - exposing the part to gaseous trimethyl aluminum (TMA);
 - stopping provision of the gaseous TMA;
 - removing gaseous TMA from the chamber;
 - exposing the part to atomic oxygen; and
 - removing atomic oxygen from the chamber,wherein in each cycle more than one monolayer of Al_2O_3 is formed.
2. (Original) The process of claim 1, wherein in each cycle a layer of Al_2O_3 3 Å thick is formed.
3. (Original) The process of Claim 1, wherein the oxygen radicals are generated remotely in a radical generator.
4. (Original) The process of Claim 1, wherein the process is carried out at room temperature.
5. - 17. (Cancelled)
18. (Previously Presented) A process of growing a thin film of Al_2O_3 on a substrate by a sequential vapor deposition process comprising a plurality of cycles, each cycle comprising:
 - exposing the part to gaseous trimethyl aluminum (TMA);
 - stopping provision of the gaseous TMA;
 - removing gaseous TMA from the chamber; and
 - exposing the part to atomic oxygen.
19. (Previously Presented) The process of Claim 18, wherein the radicals are generated remotely in a radical generator.
20. (Previously Presented) The process of Claim 18, wherein the process is carried out at room temperature.